

METHOD FOR THE HEAT TREATMENT OF SUBSTRATES

Abstract of the Disclosure

A substrate undergoes a semiconductor fabrication process at different temperatures in a reactor without changing the temperature of the reactor. The substrate is held suspended by flowing gas between two heated surfaces of the reactor. Moving the two heated surfaces in close proximity with the substrate for a particular time duration heats the substrate to a desired temperature. The desired temperature is then maintained by distancing the heated surfaces from the substrate and holding the heated surface at the increased distance to minimize further substrate heating.

W:\DOCS\ZYW\ZYW-2284.DOC
092303